

# A 0.097 mm<sup>2</sup> 4.0-31.8 GHz Inverter-based LNA With Parallel-Series Transformer Feedback

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# Introduction

# Advantages of the multi-band

- To support multiple wireless protocols within a single architecture, enabling flexible and efficient spectrum usage.
- The reduced system cost, area, and power by consolidating functionality.

#### The necessity of a Low Noise Amplifier (LNA)

- A key gain stage in the receiver that defines system sensitivity and dynamic range.
- To amplify weak incoming signals while minimizing additional noise.

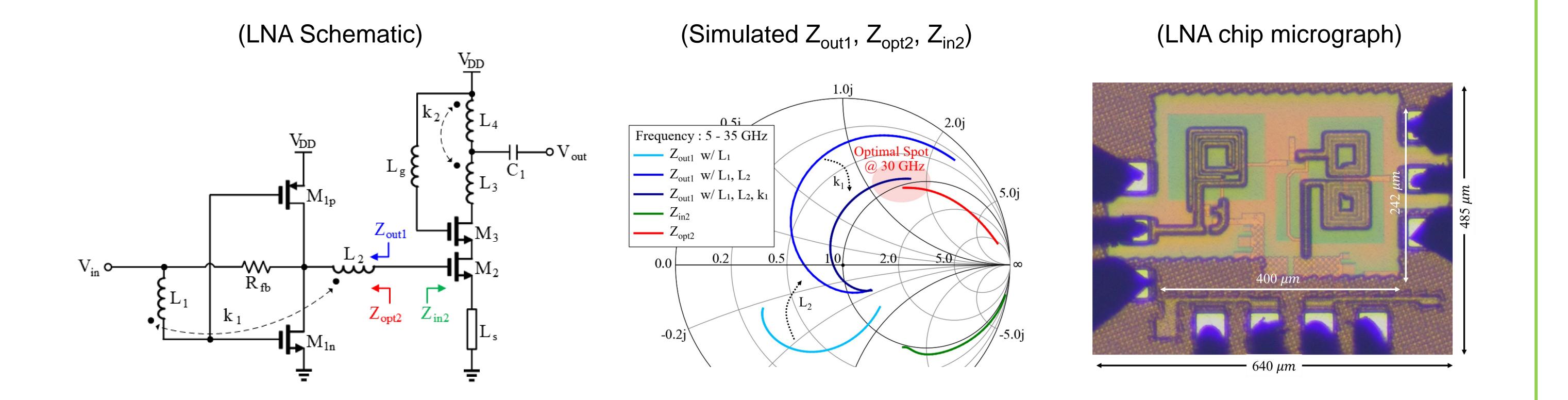
# Design

# Parallel-series transformer feedback

- The parallel and series inductors optimize NF at high frequencies, enabling flat noise performance.
- The coupling between the inductors provides wideband input matching, similar to a source-degenerative inductor.
- The parallel inductor reduces the first-stage noise contribution from 32.2 % at 5 GHz to 24.6 % at 30 GHz.
- The series inductor alleviates the trade-off between NF and  $S_{21}$  by aligning  $Z_{out1}$  with  $Z_{opt2}$

# Inverter-based amplifier

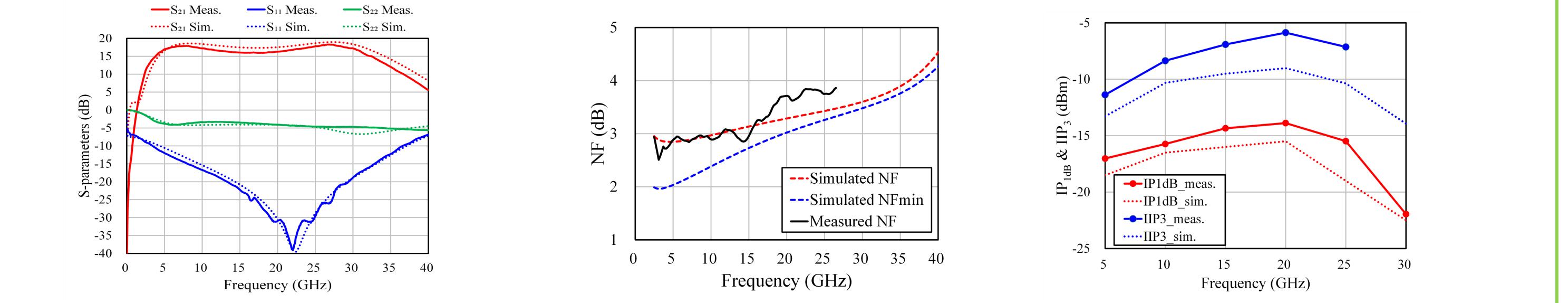
- Achieving high gain from low frequencies facilitates the realization of a wide 3-dB bandwidth.
- Self-biasing via resistive feedback simplifies the layout, requiring only two bias lines.



# Results

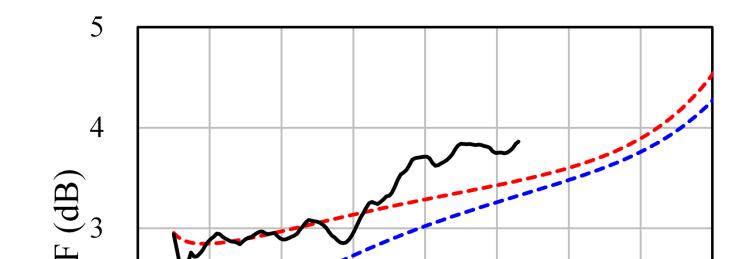
#### S-parameters measurement

- Peak S<sub>21</sub> : 18.3 dB
- 3-dB BW : 27.8 GHz (4.0–31.8 GHz)



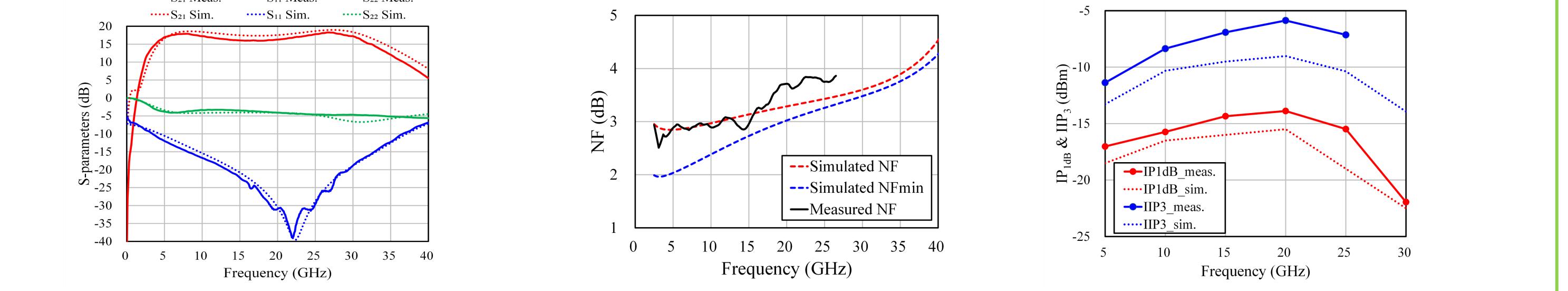
## Noise figure measurement

- NF : 2.72-3.86 dB
- $\triangle$ NF/BW : 0.02 dB/GHz



## Linearity measurement

- IIP<sub>3</sub>: -11.4 -5.87 dBm
- IP<sub>1dB</sub> : -21.9 -13.9 dBm





- We have developed a wideband inverter-based LNA in a 28-nm CMOS process.
- The LNA demonstrates wide 3-dB BW with 4.0-31.8 GHz and low NF with 2.72-3.86 dB.

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